

# BD136/138/140

# Medium Power Linear and Switching Applications

• Complement to BD135, BD137 and BD139 respectively



# **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parar	neter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: BD136	- 45	V
		: BD138	- 60	V
		: BD140	- 80	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: BD136	- 45	V
		: BD138	- 60	V
		: BD140	- 80	V
V <sub>EBO</sub>	Emitter-Base Voltage		- 5	V
I <sub>C</sub>	Collector Current (DC)		- 1.5	Α
I <sub>CP</sub>	Collector Current (Pulse)		- 3.0	Α
I <sub>B</sub>	Base Current		- 0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		12.5	W
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)		1.25	W
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		- 55 ~ 150	°C

## **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage					
	: BD136	$I_C = -30 \text{mA}, I_B = 0$	- 45			V
	: BD138		- 60			V
	: BD140		- 80			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -30V, I_{E} = 0$			- 0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 10	μΑ
h <sub>FE1</sub>	* DC Current Gain	$V_{CE} = -2V, I_{C} = -5mA$	25			
h <sub>FE2</sub>		$V_{CE} = -2V, I_{C} = -0.5A$	25			
$h_{FE3}$		$V_{CE} = -2V, I_{C} = -150mA$	40		250	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 500mA, I <sub>B</sub> = - 50mA			- 0.5	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage	$V_{CE} = -2V, I_{C} = -0.5A$			- 1	V

<sup>\*</sup> Pulse Test: PW=350μs, duty Cycle=2% Pulsed

# **h**<sub>FE</sub> Classificntion

h 40 100 63 160 100 35	Classification	6	10	16
11FE3 40 ~ 100 65 ~ 160 100 ~ 25		40 ~ 100		100 ~ 250

# **Typical Characteristics**

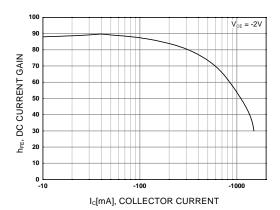


Figure 1. DC current Gain

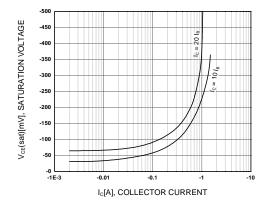


Figure 2. Collector-Emitter Saturation Voltage

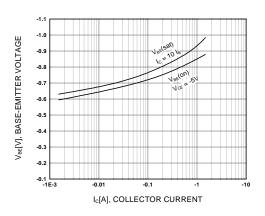


Figure 3. Base-Emitter Voltage

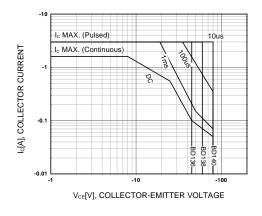


Figure 4. Safe Operating Area

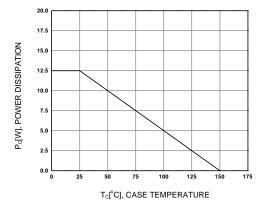
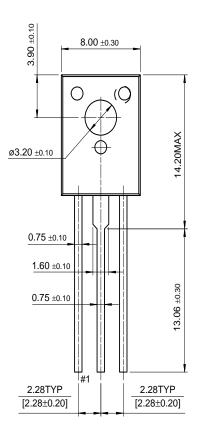


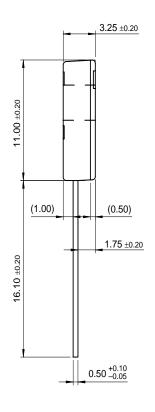
Figure 5. Power Derating

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BD136/138/140

TO-126





Dimensions in Millimeters

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